



## PATENT ABSTRACTS OF JAPAN

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(54) **SEMICONDUCTOR DEVICE AND METHOD OF  
MANUFACTURING THE SAME, AND METHOD  
OF FORMING INSULATION FILM**

(57) Abstract:

**PROBLEM TO BE SOLVED:** To increase the resistance with respect to various chemicals and plasma used in semiconductor manufacturing processes by improving the adhesiveness of a low-density film having low permittivity.

**SOLUTION:** The surface of the low-density film, having a low permittivity, is plasma-treated to form a very fine surface modified layer.

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